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RSF010P03

Transistors

4V Drive Pch MOSFET

RSF010P03

●Structure

Silicon P-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) High speed switching.

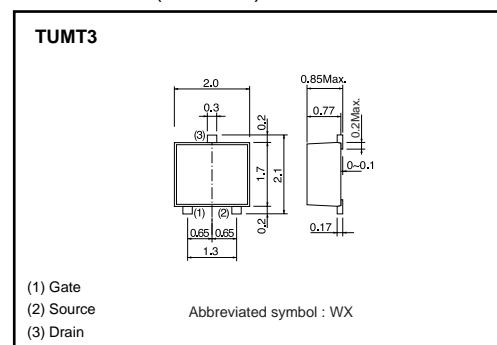
●Applications

Switching

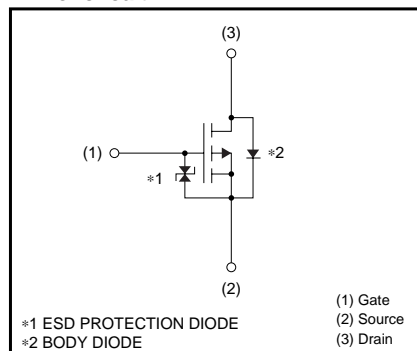
●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSF010P03		○

●Dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V _{DSS}	-30	V	
Gate-source voltage	V _{GSS}	±20	V	
Drain current	Continuous	I _D	±1	A
	Pulsed	I _{DP} *1	±4	A
Source current (Body diode)	Continuous	I _S	-0.3	A
	Pulsed	I _{SP} *1	-4	A
Total power dissipation	P _D *2	0.8	W	
Channel temperature	T _{ch}	150	°C	
Range of storage temperature	T _{stg}	-55 to +150	°C	

*1 Pw≤10μs, Duty cycle≤1%
 *2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th(ch-a)} *	156	°C/W

* Mounted on a ceramic board

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	–30	–	–	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	–1.0	–	–2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	250	350	m Ω	$I_D = -1A, V_{GS} = -10V$
		–	400	560	m Ω	$I_D = -0.5A, V_{GS} = -4.5V$
		–	450	630	m Ω	$I_D = -0.5A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} $ *	0.5	–	–	S	$V_{DS} = -10V, I_D = -0.5A$
Input capacitance	C_{iss}	–	120	–	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	–	27	–	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	–	17	–	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	8	–	ns	$V_{DD} = -15V$ $I_D = -0.5A$
Rise time	t_r *	–	11	–	ns	$V_{GS} = -10V$
Turn-off delay time	$t_{d(off)}$ *	–	20	–	ns	$R_L = 30\Omega$ $R_G = 10\Omega$
Fall time	t_f *	–	12	–	ns	
Total gate charge	Q_g	–	1.9	–	nC	$V_{DD} = -15V, V_{GS} = -5V$
Gate-source charge	Q_{gs}	–	0.7	–	nC	$I_D = -1A$
Gate-drain charge	Q_{gd}	–	0.4	–	nC	$R_L = 15\Omega, R_G = 10\Omega$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	–1.2	V	$I_S = -0.3A, V_{GS} = 0V$

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●Electrical characteristics curves

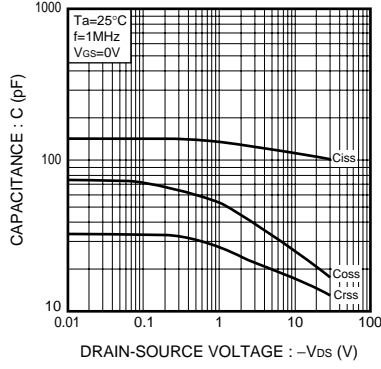


Fig.1 Typical Capacitance vs. Drain-Source Voltage

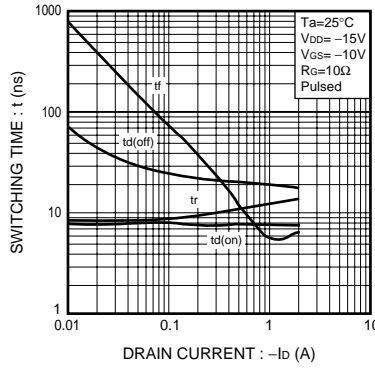


Fig.2 Switching Characteristics

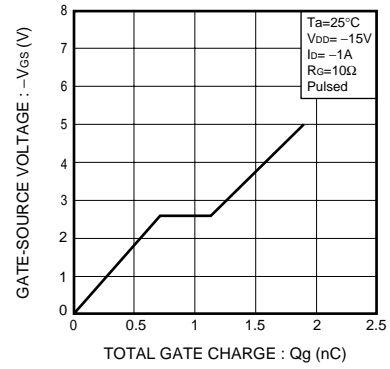


Fig.3 Dynamic Input Characteristics

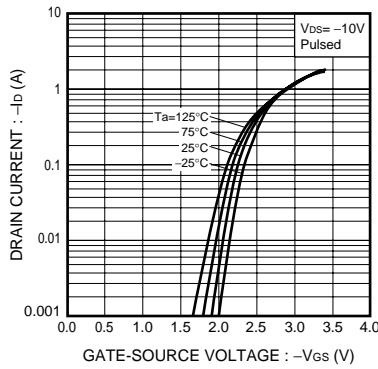


Fig.4 Typical Transfer Characteristics

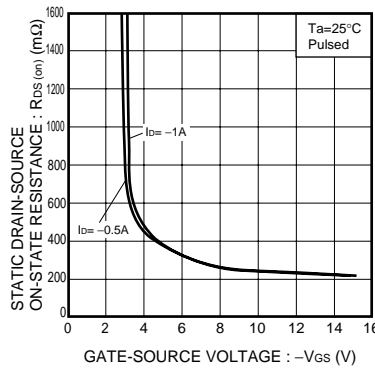


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

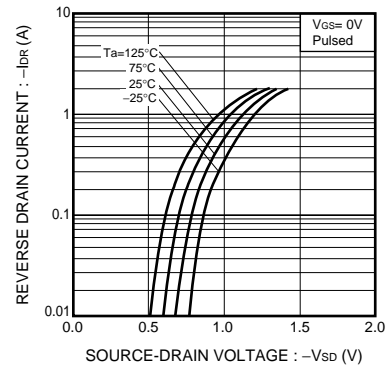


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

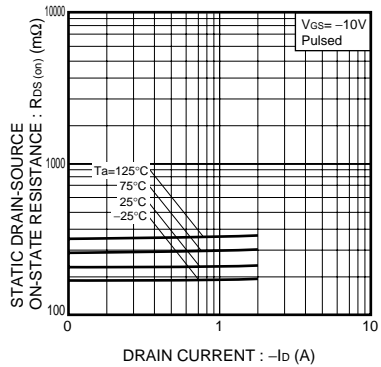


Fig.7 Static Drain-Source On-State Resistance vs. Drain current (I)

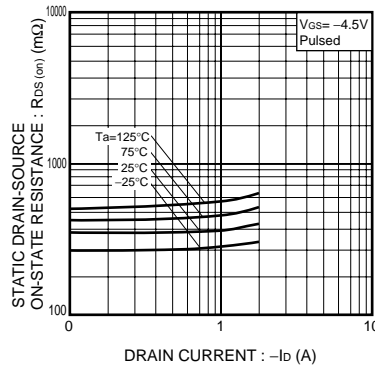


Fig.8 Static Drain-Source On-State Resistance vs. Drain current (II)

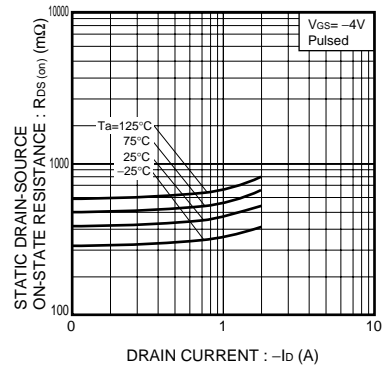


Fig.9 Static Drain-Source On-State Resistance vs. Drain current (III)

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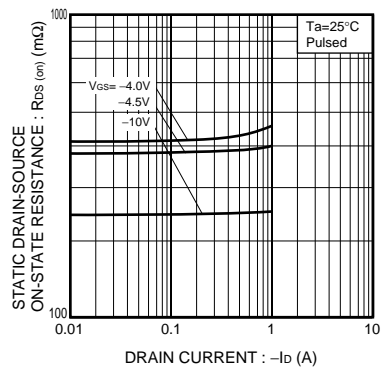


Fig.10 Static Drain-Source On-State Resistance vs. Drain current (I_V)

Appendix

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